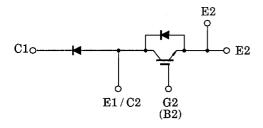
TOSHIBA GTR Module Silicon N Channel IGBT

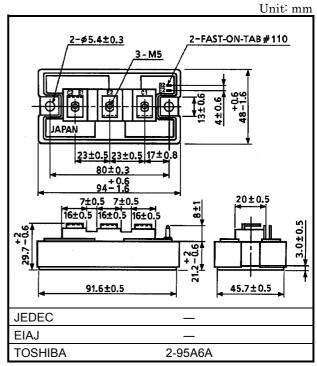
# MG100Q1ZS50

# High Power Switching Applications Motor Control Applications

- High input impedance
- High speed: tf = 0.3µs (Max)
  @Inductive load
- Low saturation voltage
  - $: V_{CE (sat)} = 3.6V (Max)$
- Enhancement-mode
- The electrodes are isolated from case.

### **Equivalent Circuit**





Weight: 255g

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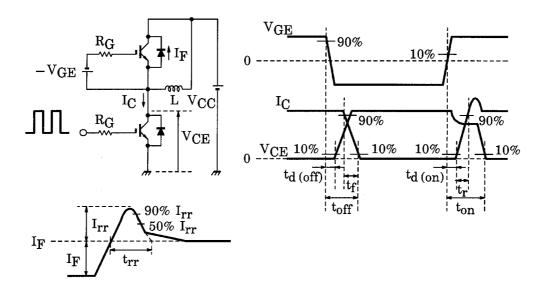
#### **Maximum Ratings (Ta = 25°C)**

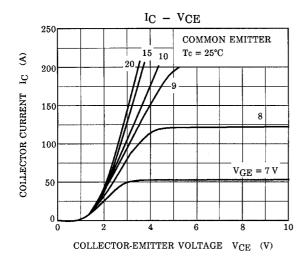
Characteristic		Symbol	Rating	Unit	
Collector-emitter voltage		V <sub>CES</sub>	1200	V	
Gate-emitter voltage		V <sub>GES</sub>	±20	V	
Collector current	DC	I <sub>C</sub> (25°C / 80°C) 150 / 100		- A	
	1ms	I <sub>CP</sub> (25°C / 80°C) 300 / 200			
Forward current	DC	I <sub>F</sub>	100	A	
Forward Current	1ms	I <sub>FM</sub>	200		
Collector power dissipation (Tc = 25°C)		PC	660	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T <sub>stg</sub>	<b>−</b> 40 ~ 125	°C	
Isolation voltage		V <sub>Isol</sub>	2500 (AC 1 min.)	V	
Screw torque (Terminal / mounting)		_	3/3	N·m	

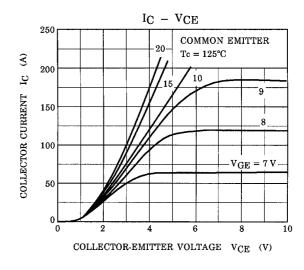
## **Electrical Characteristics (Ta = 25°C)**

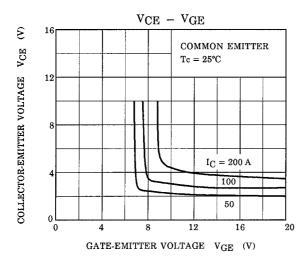
Cha	racteristic	Symbol	Test Condition		Min	Тур.	Max	Unit
Gate leakage curr	ent	I <sub>GES</sub>	V <sub>GE</sub> = ±20V, V <sub>CE</sub> = 0		_	_	±500	nA
Collector cut-off c	urrent	I <sub>CES</sub>	V <sub>CE</sub> = 1200V, V <sub>GE</sub> = 0		_	_	2.0	mA
Gate-emitter cut-o	ff voltage	V <sub>GE (off)</sub>	I <sub>C</sub> = 100mA, V <sub>CE</sub> = 5V		3.0	_	6.0	V
Collector-emitter saturation voltage		V <sub>CE (sat)</sub>	I <sub>C</sub> = 100A, V <sub>GE</sub> = 15V	T <sub>j</sub> = 25°C	_	2.8	3.6	V
				T <sub>j</sub> = 125°C	_	3.1	4.0	
Input capacitance		C <sub>ies</sub>	V <sub>CE</sub> = 10V, V <sub>GE</sub> = 0, f = 1MHz		_	12.0	_	nF
Switching time	Turn-on delay time	t <sub>d(on)</sub>	Inductive load V <sub>CC</sub> = 600V I <sub>C</sub> = 100A,		_	0.05	_	
	Rise time	t <sub>r</sub>			_	0.05	_	μs
	Turn-on time	t <sub>on</sub>			_	0.2	_	
	Turn-off delay time	t <sub>d(off)</sub>	$V_{GE} = \pm 15V$ $R_G = 9.1\Omega$		_	0.5	_	
	Fall time	t <sub>f</sub>		(Note 1)	_	0.1	0.3	
	Turn-off time	t <sub>off</sub>			_	0.6	_	
Forward voltage		V <sub>F</sub>	I <sub>F</sub> = 100A, V <sub>GE</sub> = 0		_	2.4	3.5	V
Reverse recovery time		t <sub>rr</sub>	$I_F = 100A, V_{GE} = -10V$ di / dt = 700A / $\mu$ s (Note 1)		_	0.1	0.25	μs
Thermal resistance		R <sub>th (j-c)</sub>	Transistor stage		_	_	0.16	°C/W
			Diode stage		_	_	0.47	

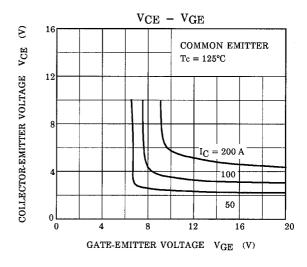
Note 1: Switching time and reverse recovery time test circuit & timing chart

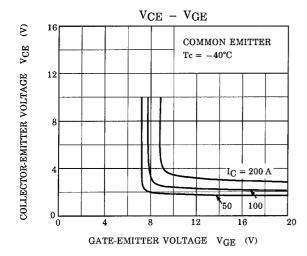


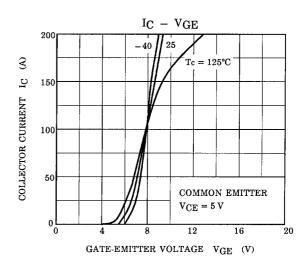




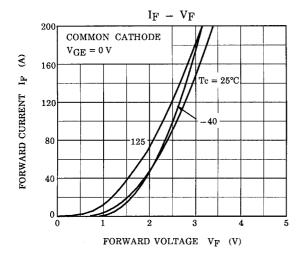


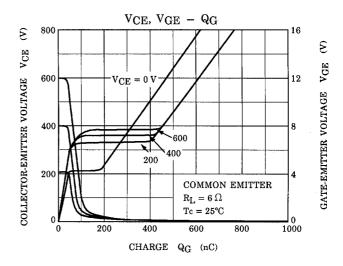


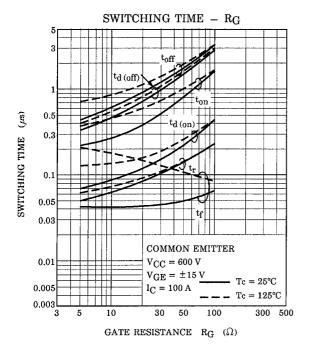


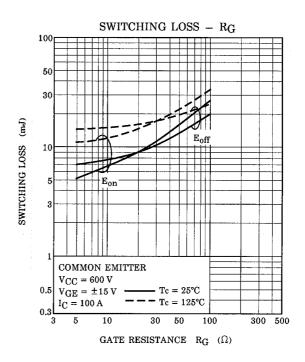


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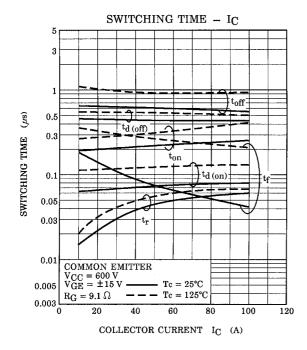


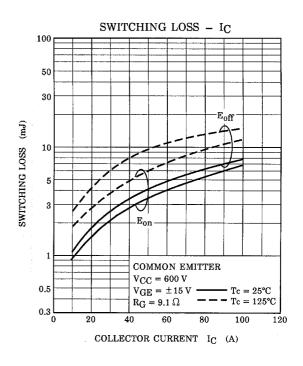


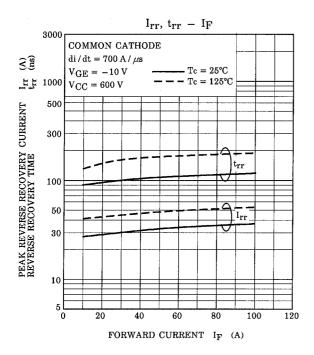


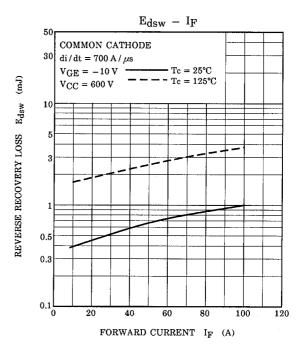


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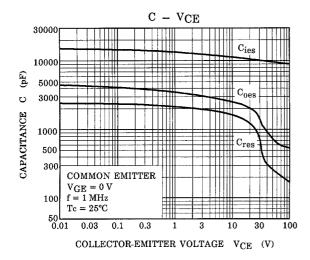


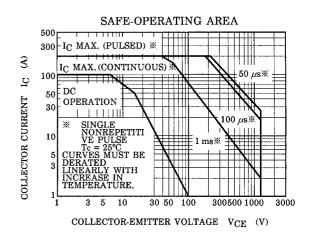


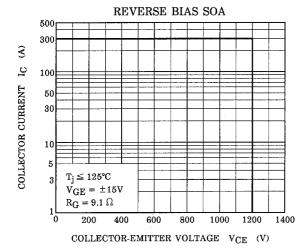


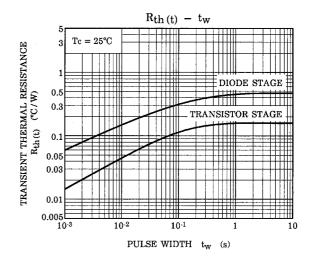


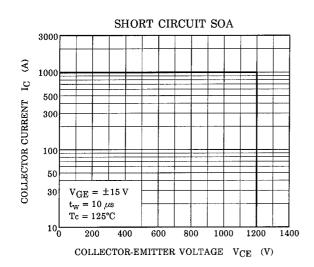
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